

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

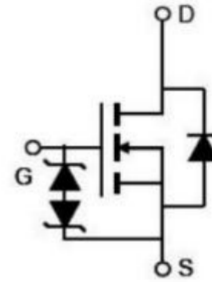
Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

$V_{DS\ min@T_{jmax}}$	650	V
$R_{DS(ON)TYP}$	180	m Ω
I_D	18	A
Qg	22.8	nC

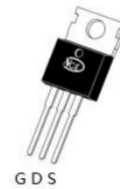


Schematic diagram

✧ Intrinsic fast-recovery body diode

Package Marking And Ordering Information

Device	Device Package	Marking
NCE60NF200	TO-220	NCE60NF200



TO-220

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	600	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$) DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	18	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	12.6	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	54	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	150	W
Derate above 25°C		1.0	W/ $^\circ\text{C}$
Avalanche current(Note 1)	I_{AS}	3.5	A
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$,	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^\circ\text{C}$

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	1.0	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current(Tc=25°C)	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$			10	μA
Zero Gate Voltage Drain Current(Tc=125°C)	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$			300	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 200	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3.5	4.2	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=9A$		180	200	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0\text{MHz}$		1157		pF
Output Capacitance	C_{oss}			60		pF
Reverse Transfer Capacitance	C_{rss}			1.5		pF
Total Gate Charge	Q_g	$V_{DS}=400V, I_D=9A,$ $V_{GS}=10V$		22.8		nC
Gate-Source Charge	Q_{gs}			9.1		nC
Gate-Drain Charge	Q_{gd}			6		nC
Gate plateau voltage	V_{gp}			6.5		V
Intrinsic gate resistance	R_G	$f = 1 \text{ MHz open drain}$		20		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=9A,$ $R_G=1.7\Omega, V_{GS}=10V$		25		nS
Turn-on Rise Time	t_r			16		nS
Turn-Off Delay Time	$t_{d(off)}$			75		nS
Turn-Off Fall Time	t_f			9		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_C=25^{\circ}\text{C}$			18	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				54	A
Forward On Voltage	V_{SD}	$T_j=25^{\circ}\text{C}, I_{SD}=18A, V_{GS}=0V$		1.0	1.2	V
Reverse Recovery Time	t_{rr}	$T_j=25^{\circ}\text{C}, I_f=9A,$ $di/dt=100A/\mu s$		90		nS
Reverse Recovery Charge	Q_{rr}			0.32		μC
Peak Reverse Recovery Current	I_{rm}			7		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area



Figure2. Capacitance

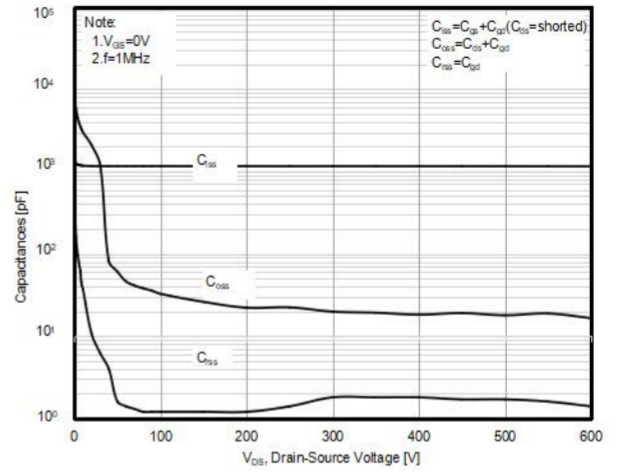


Figure3. Transfer characteristics

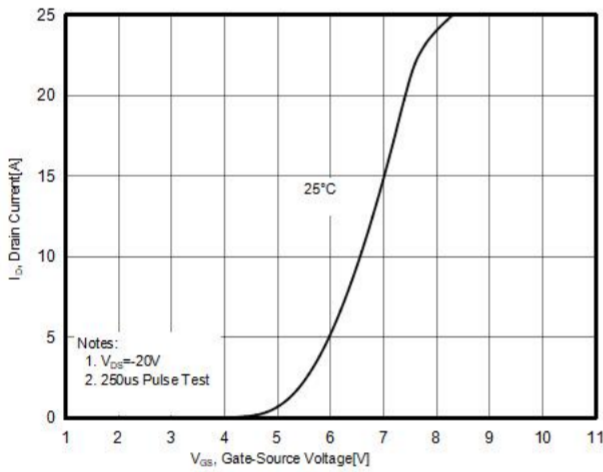


Figure4. Output characteristics

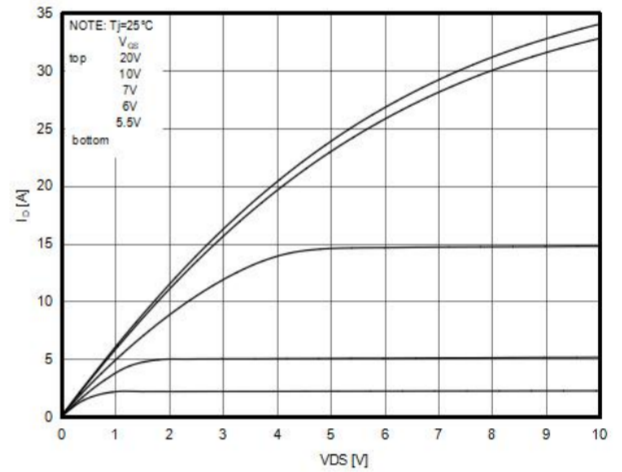


Figure5. $R_{DS(ON)}$ vs Junction Temperature

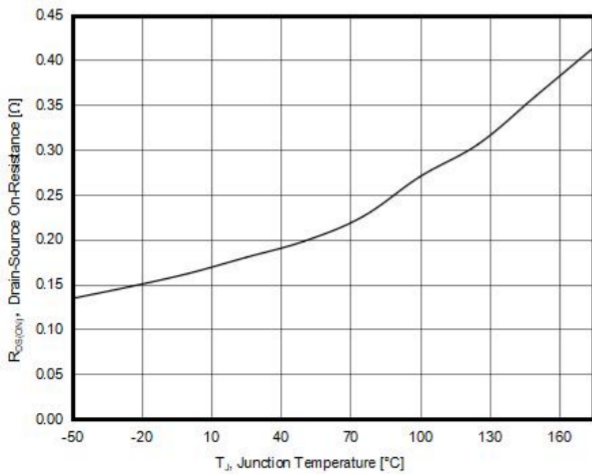


Figure6. BV_{DSS} vs Junction Temperature

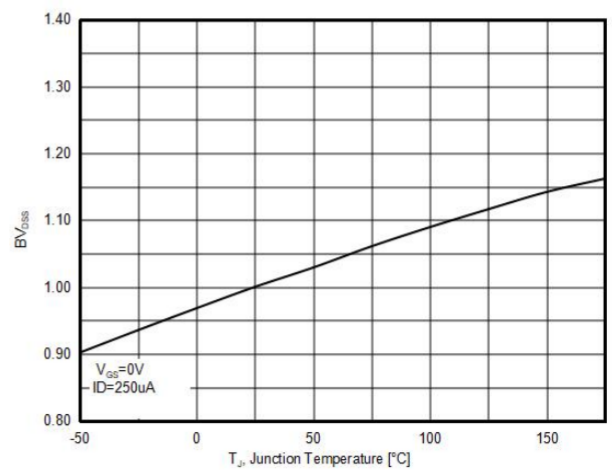


Figure7. Maximum I_D vs Junction Temperature

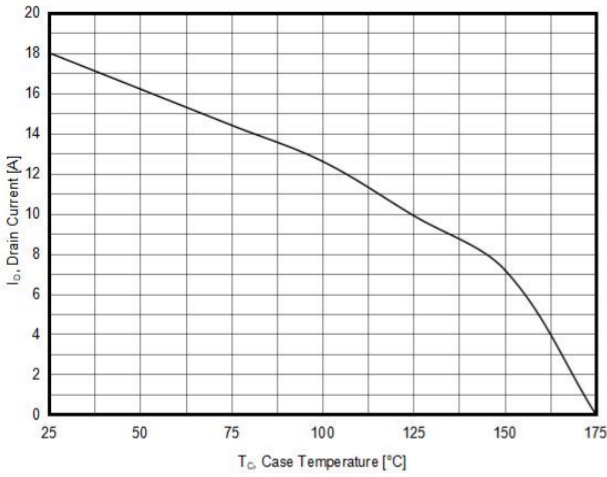


Figure8. Gate charge waveforms

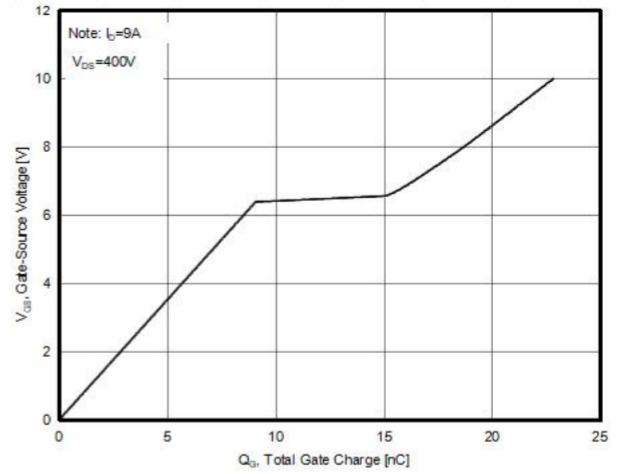


Figure9. Static drain-source on resistance

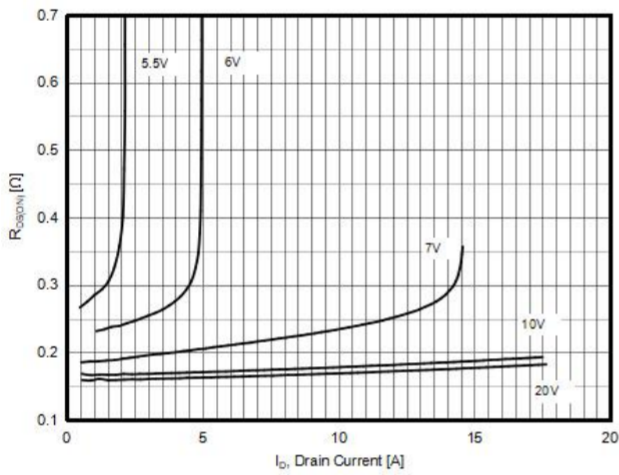
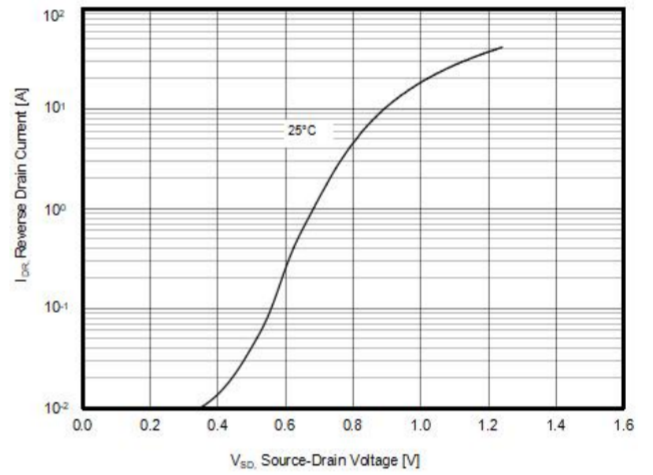
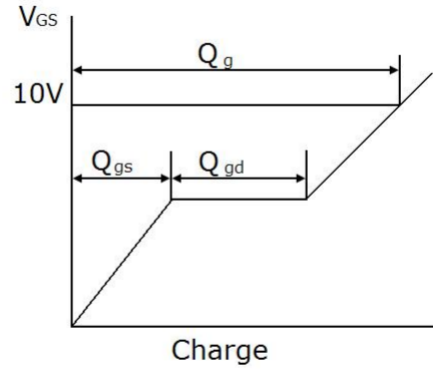
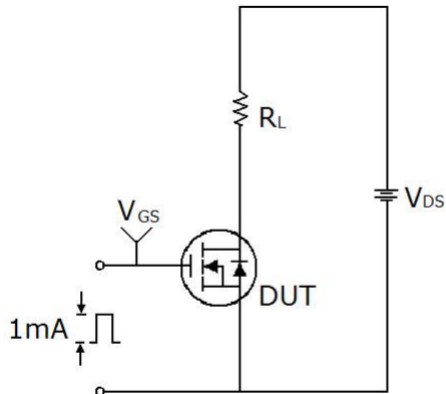


Figure10. Source-Drain Diode Forward Voltage

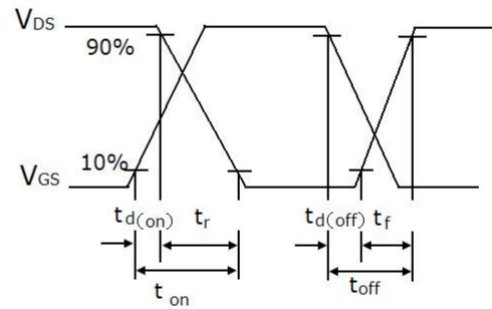
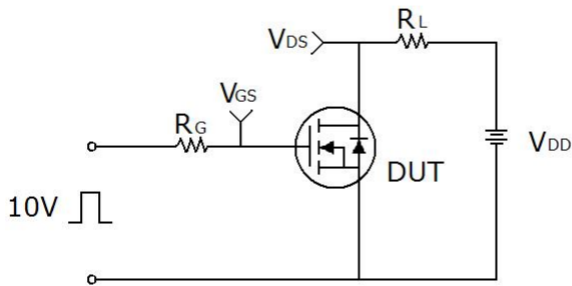


Test circuit

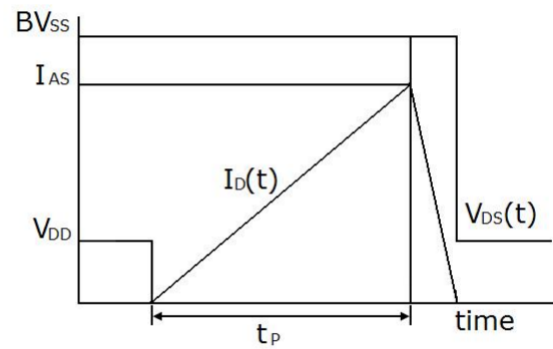
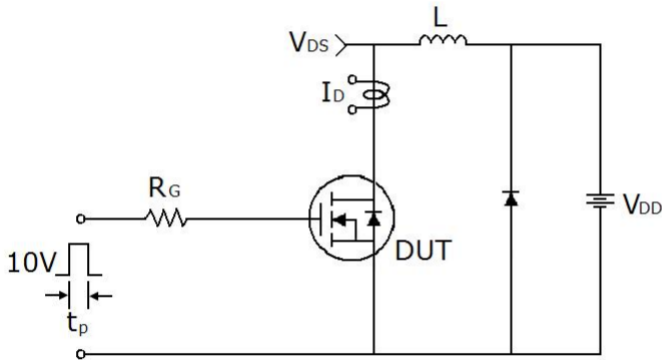
1) Gate charge test circuit & Waveform



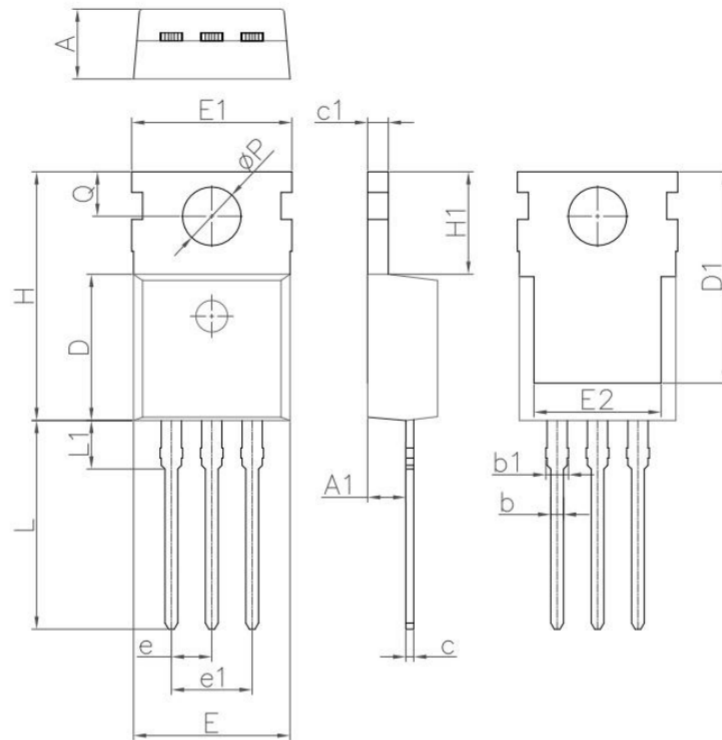
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

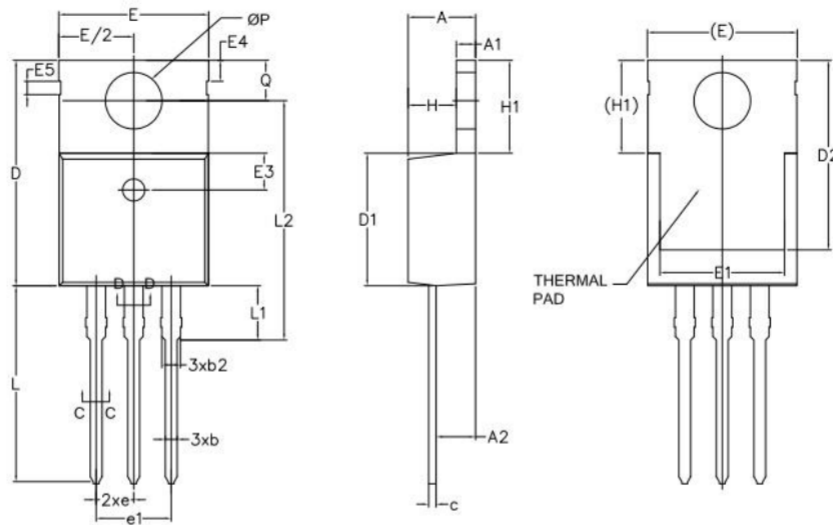


TO-220-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.20	4.60	0.165	0.181
A1	2.25	2.55	0.089	0.100
b	0.70	0.90	0.028	0.035
b1	1.17	1.37	0.046	0.054
c	0.33	0.65	0.013	0.026
c1	1.20	1.40	0.047	0.055
D	8.95	9.75	3.524	3.839
D1	13.10	13.50	5.157	5.315
E	9.74	10.04	3.835	3.953
E1	9.91	10.25	3.902	4.035
E2	7.90	8.10	3.110	3.189
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	15.45	15.85	6.083	6.240
H1	6.30	6.60	2.480	2.598
L	12.90	13.40	5.079	5.276
L1	2.85	3.25	1.122	1.280
Q	2.65	2.95	1.043	1.161
ΦP	3.40	3.80	1.339	1.496

TO-220-J Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.47	4.67	0.176	0.184
A1	1.20	1.40	0.047	0.055
A2	2.35	2.90	0.093	0.114
b	0.71	0.91	0.028	0.036
b1	0.71	0.86	0.028	0.034
b2	1.22	1.36	0.048	0.054
c	0.47	0.60	0.019	0.024
c1	0.47	0.55	0.019	0.022
D	14.70	15.80	0.579	0.622
D1	8.90	9.47	0.350	0.373
D2	11.75	13.60	0.463	0.535
E	9.70	10.37	0.382	0.408
E1	7.00	8.89	0.276	0.350
E2	9.80	10.20	0.386	0.402
E3	2.40	2.60	0.094	0.102
E4	1.27	1.57	0.050	0.062
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	3.00	3.40	0.118	0.134
L	12.90	14.80	0.508	0.583
L1	2.54	3.84	0.100	0.151
L2	12.13	16.50	0.478	0.650
ΦP	3.60	3.90	0.142	0.154
Q	2.65	2.95	0.104	0.116

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